

isc Silicon NPN Power Transistor

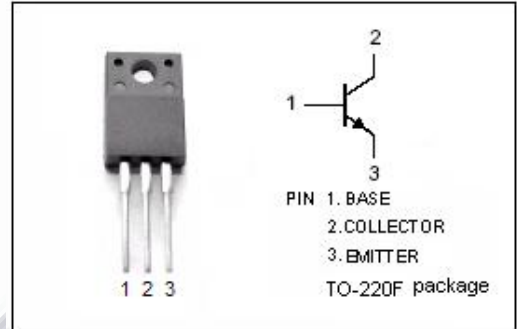
2SC4495

DESCRIPTION

- Fast switching speed
- Silicon NPN planar diffused planar transistor
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

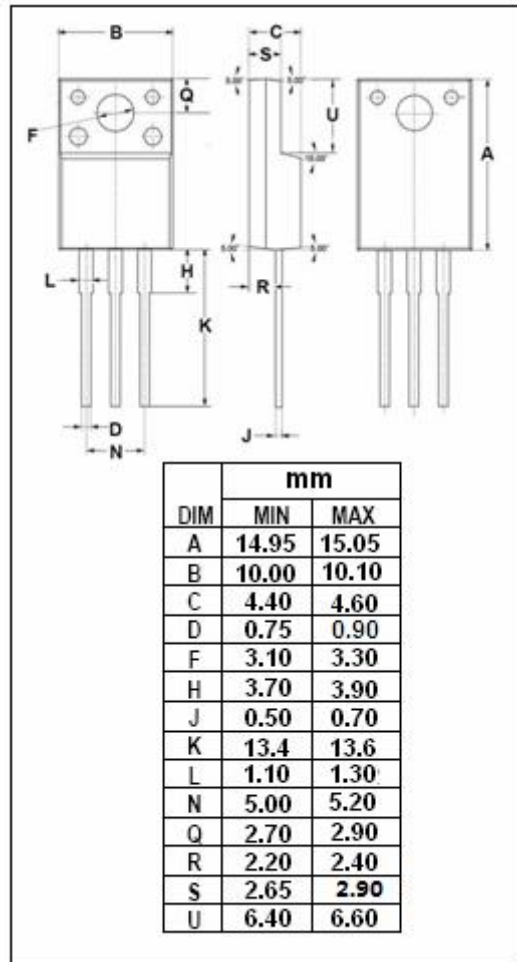
APPLICATIONS

- Audio temperature compensation and general purpose



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current-Continuous	3	A
I _B	Base Current-Continuous	1	A
P _C	Collector Power Dissipation @T _C =25°C	25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



isc Silicon NPN Power Transistor**2SC4495****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	50			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1A; I _B = 20mA			0.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 80V; I _E = 0			100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			100	μ A
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 4V	500			
f _T	Current-Gain—Bandwidth Product	I _E = -0.1A; V _{CE} = 12V		40		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f= 1MHz		30		pF